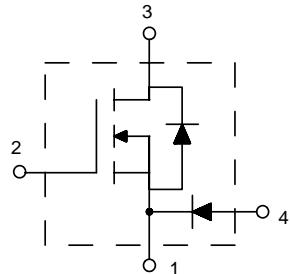
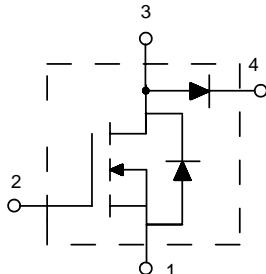


HiPerFET™
Power MOSFETs
IXFN44N50U2
IXFN44N50U3
IXFN48N50U2
IXFN48N50U3

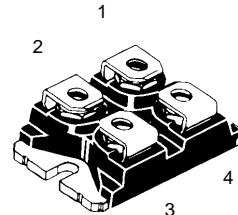
V_{DSS}	I_D (cont)	R_{DS(on)}	t_{rr}
500 V	44 A	0.12 Ω	35 ns
500 V	48 A	0.10 Ω	35 ns

Buck & Boost Configurations for PFC & Motor Control Circuits

Preliminary data



	Symbol	Test Conditions	Maximum Ratings	
HiPerFET MOSFET	V_{DSS}	T _J = 25°C to 150°C	500	V
	V_{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	500	V
	V_{GS}	Continuous	±20	V
	V_{GSM}	Transient	±30	V
	I_{D25}	T _C = 25°C	44N50 48N50	44 48 A
	I_{DM}	T _C = 25°C, pulse width limited by max. T _{JM}	44N50 48N50	176 192 A
	I_{AR}	T _C = 25°C	24	A
	E_{AR}	Repetitive	30	mJ
DIODE	dv/dt	I _S ≤ I _{DM} , -di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 2 Ω	5	V/ns
	P_D	T _C = 25°C	520	W
	V_{RRM}		600	V
	I_{FAVM}	T _C = 70°C; rectangular, d = 0.5	60	A
CASE	I_{FRM}	tp < 10 μs; pulse width limited by T _J	800	A
	P_D	T _C = 25°C	180	W
	T_J		-40 ... +150	°C
	T_{JM}		150	°C
	T_{stg}		-40 ... +150	°C
	V_{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	t = 1 min t = 1 s	2500 3000 V~
	M_d	Mounting torque Terminal connection torque (M4)	1.5/13 Nm/lb.in. 1.5/13 Nm/lb.in.	
	Weight		30	g

miniBLOC, SOT-227 B

Features

- Popular Buck & Boost circuit topologies
- International standard package miniBLOC SOT-227B
- Aluminium nitride isolation
 - high power dissipation
- Isolation voltage 3000 V~
- Low R_{DS(on)} HDMOS™ process
- Rugged polysilicon gate cell structure
- Low drain-to-case capacitance (<60 pF)
 - reduced RFI
- Ultra-fast FRED diode with soft reverse recovery

Applications

- Power factor controls and buck regulators
- DC servo and robotic drives
- DC choppers
- Switch reluctance motor controls

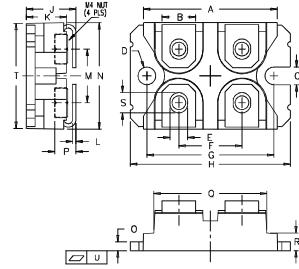
Advantages

- Easy to mount with 2 screws
- Space savings
- Tightly coupled FRED

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}$	500			V
$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 8 \text{ mA}$	2		4	V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}, V_{DS} = 0$			± 200	nA
I_{DSS}	$V_{DS} = 0.8 V_{DSS}$ $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		400 2	μA mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 0.5 I_{D25}$ 44N50 48N50 Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $\delta \leq 2 \%$	44N50 48N50		0.12 0.10	Ω

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
g_{fs}	$V_{DS} = 10 \text{ V}, I_D = 0.5 I_{D25}$, pulse test	22	42		S
C_{iss}	$\left. \begin{array}{l} C_{oss} \\ C_{rss} \end{array} \right\} V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	8400			pF
C_{oss}		900			pF
C_{rss}		280			pF
$t_{d(on)}$	$\left. \begin{array}{l} t_r \\ t_{d(off)} \\ t_f \end{array} \right\} V_{GS} = 10 \text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1 \Omega$ (External)	30			ns
t_r		60			ns
$t_{d(off)}$		100			ns
t_f		30			ns
$Q_{g(on)}$	$\left. \begin{array}{l} Q_{gs} \\ Q_{gd} \end{array} \right\} V_{GS} = 10 \text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$	270			nC
Q_{gs}		60			nC
Q_{gd}		135			nC
R_{thJC}		0.24			K/W
R_{thCK}		0.05			K/W

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
I_R	$T_J = 25^\circ\text{C}; V_R = V_{RRM}$ $V_R = 0.8V_{RRM}$ $T_J = 125^\circ\text{C}; V_R = 0.8V_{RRM}$			200 100 14	μA μA mA
V_F	$I_F = 70\text{A}, V_{GS} = 0 \text{ V}, T_J = 150^\circ\text{C}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $\delta \leq 2 \%$ $T_J = 25^\circ\text{C}$			1.5 1.8	V
t_{rr}	$I_I = 1\text{A}, di/dt = -200 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}, T_J = 25^\circ\text{C}$	35	50		ns
I_{RM}	$I_F = 60\text{A}, di/dt = -480 \text{ A}/\mu\text{s}, V_R = 350 \text{ V}, T_J = 100^\circ\text{C}$	19	21		A
R_{thJC}			0.7		K/W
R_{thJK}		0.05			K/W

miniBLOC, SOT-227 B


M4 screws (4x) supplied

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Fig.1 Output Characteristics

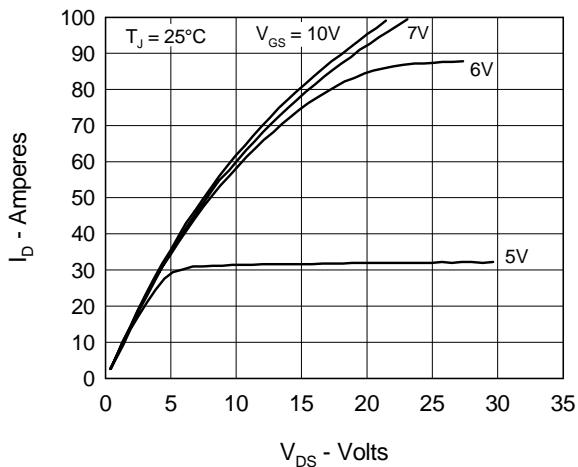


Fig.2 Input Admittance

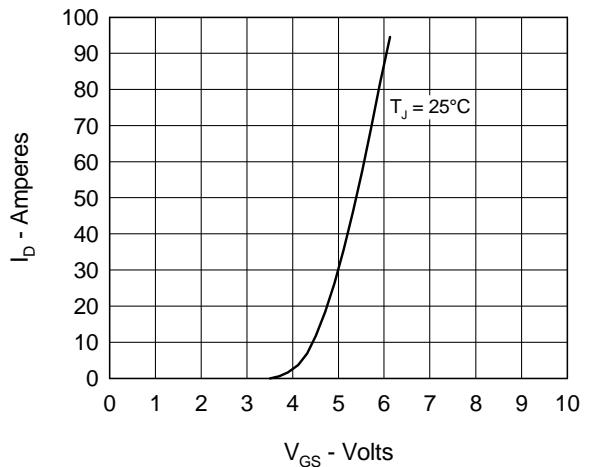


Fig.3 $R_{DS(on)}$ vs. Drain Current

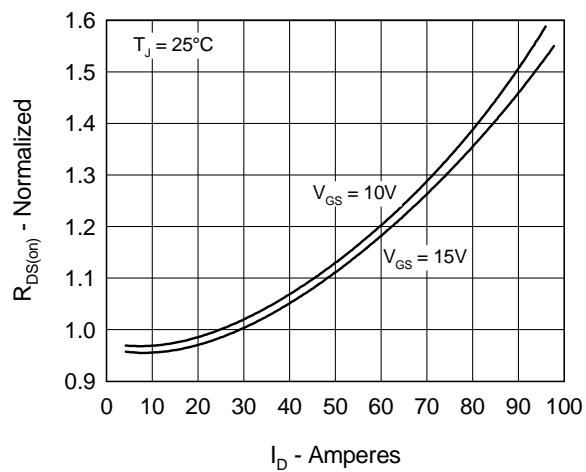


Fig.4 Temperature Dependence of Drain to Source Resistance

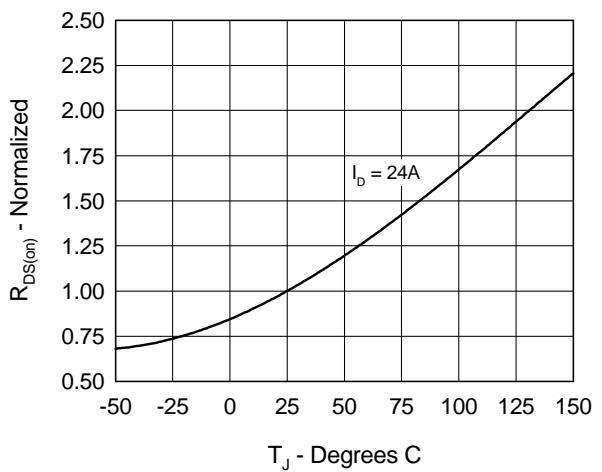


Fig.5 Drain Current vs. Case Temperature

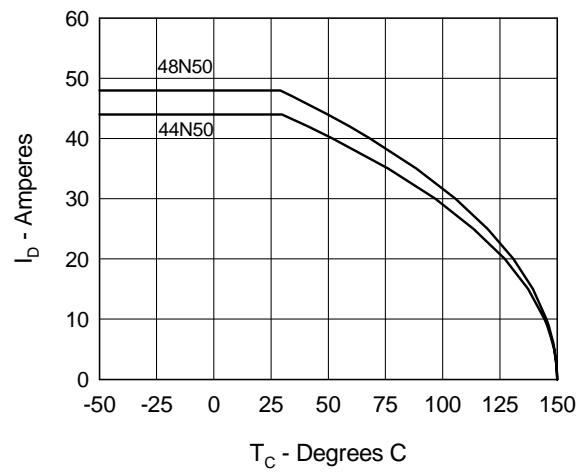


Fig.6 Temperature Dependence of Breakdown and Threshold Voltage

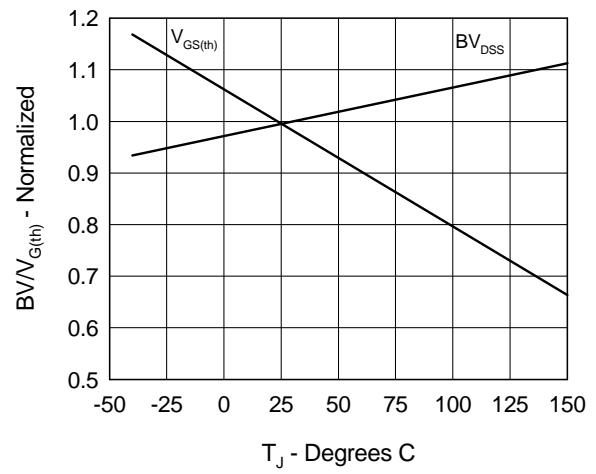


Fig.7 Gate Charge Characteristic Curve

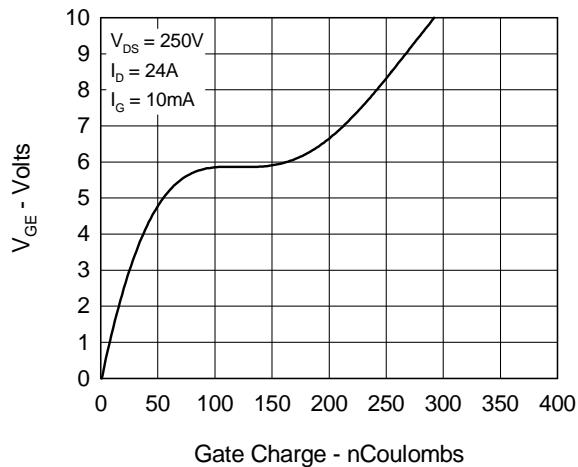


Fig.8 Capacitance Curves

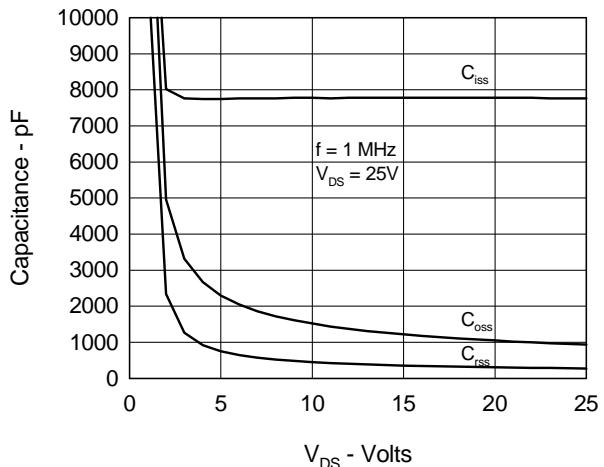


Fig.9 Source Current vs. Source to Drain Voltage

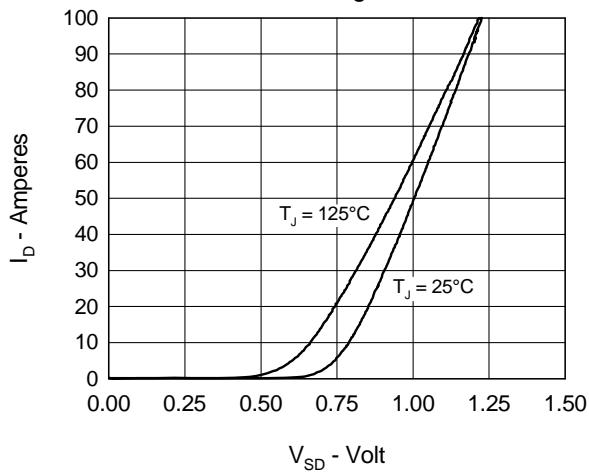
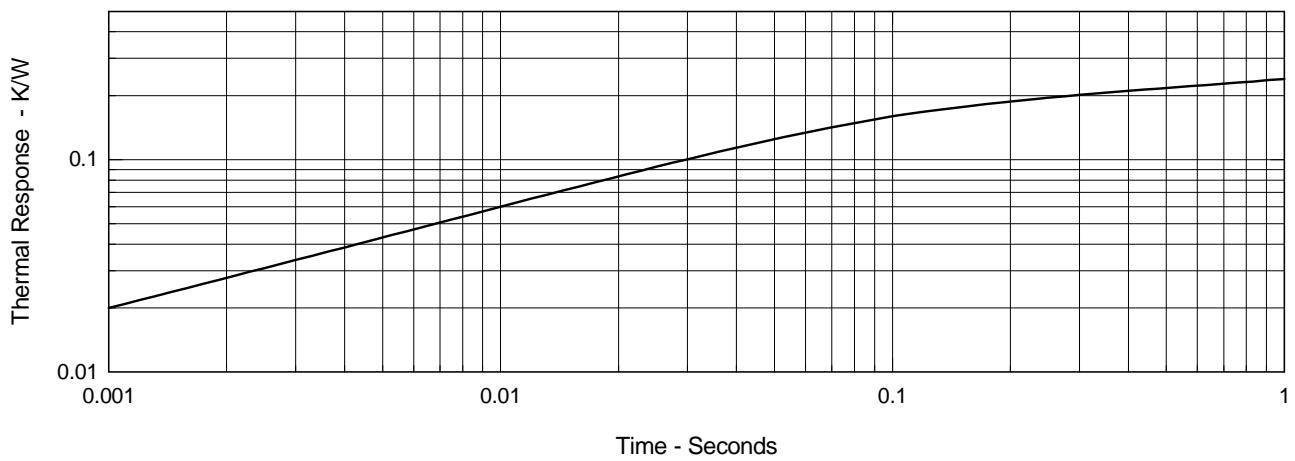


Fig.10 Transient Thermal Impedance



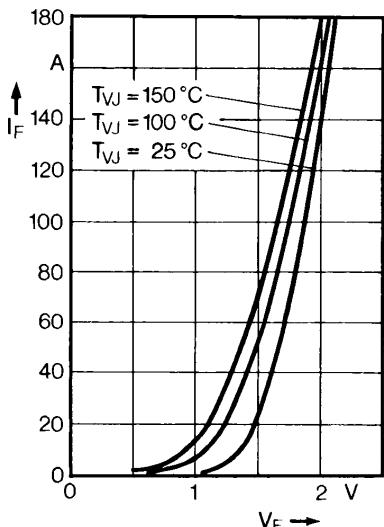


Fig. 11. Forward voltage drop.

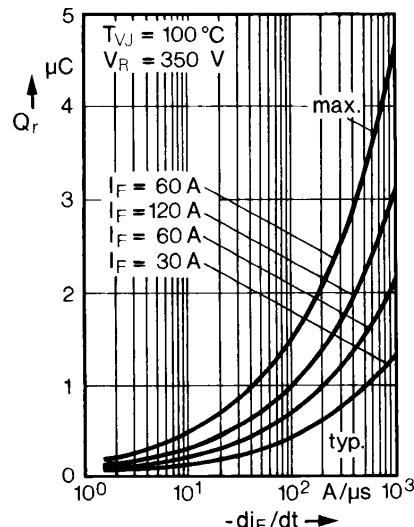


Fig. 12. Recovery charge versus $-di_F/dt$.

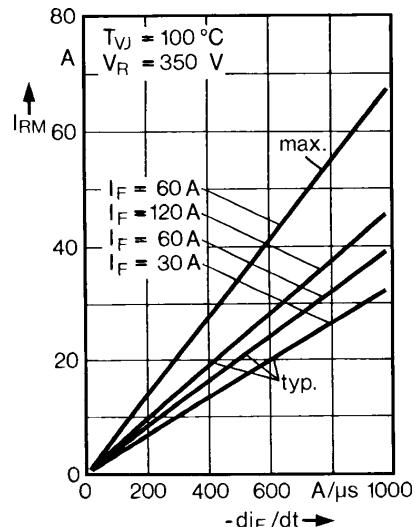


Fig. 13. Peak reverse current vs. $-di_F/dt$.

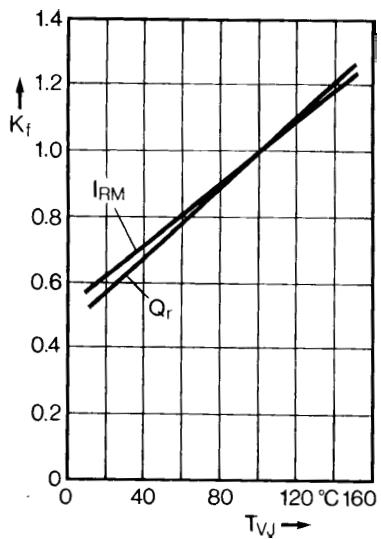


Fig. 14. Dynamic parameters versus junction temperature.

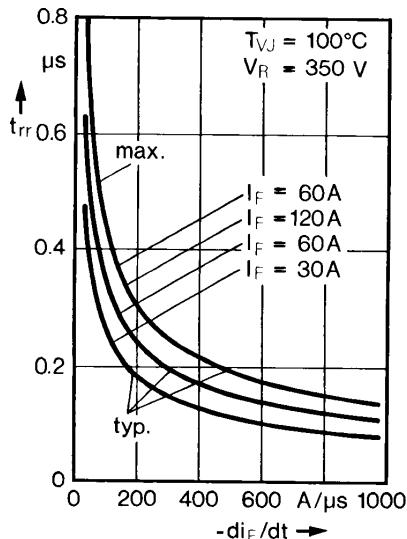


Fig. 15. Recovery time versus $-di_F/dt$.

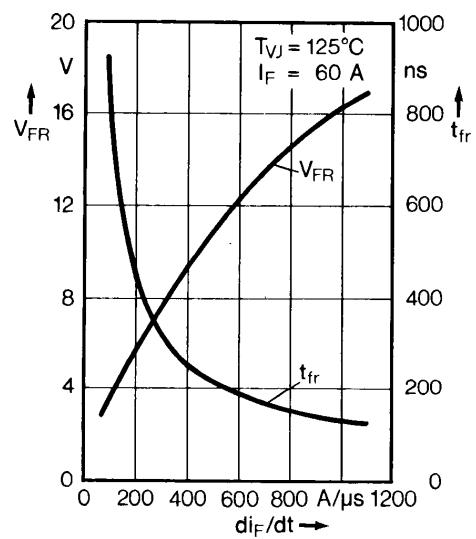


Fig. 16. Peak forward voltage and forward recovery time vs. di_F/dt .

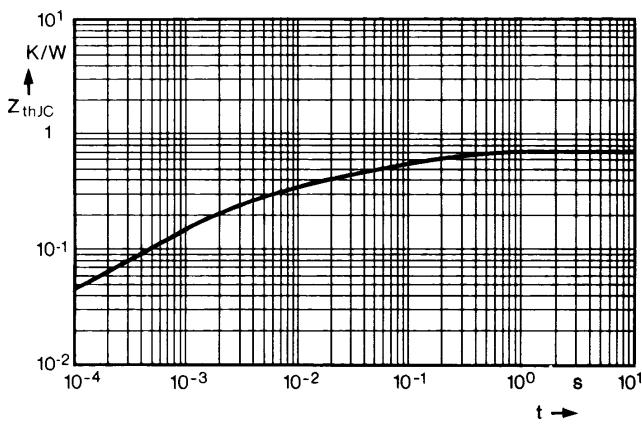


Fig. 17. Transient thermal impedance junction to case.